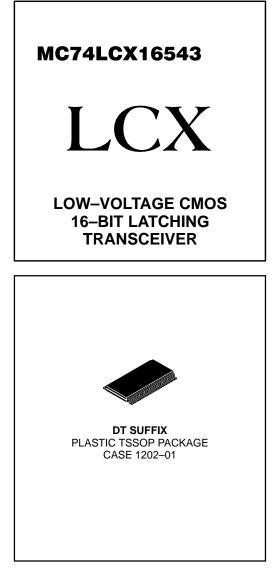
Advance Information

Low-Voltage CMOS 16-Bit Latching Transceiver With 5V-Tolerant Inputs and Outputs (3-State, Non-Inverting)

The MC74LCX16543 is a high performance, non-inverting 16-bit latching transceiver operating from a 2.7 to 3.6V supply. The device is byte controlled. Each byte has separate control inputs which can be tied together for full 16-bit operation. High impedance TTL compatible inputs significantly reduce current loading to input drivers while TTL compatible outputs offer improved switching noise performance. A V_I specification of 5.5V allows MC74LCX16543 inputs to be safely driven from 5V devices. The MC74LCX16543 is suitable for memory address driving and all TTL level bus oriented transceiver applications.

For data flow from A to B with the EAB LOW, the A-to-B Output Enable (OEAB) must be LOW in orde<u>r to</u> enable data to the B bus, as indicated in the Function <u>Table</u>. With EAB LOW, a LOW signal on the A-to-B Latch Enable (LEAB) input makes the A-to<u>-B la</u>tches transparent; a subsequent LOW-to-HIGH transition of the LEAB signal will latch th<u>e A latches</u>, and the outputs no longer change with the A inputs. With EAB and OEAB both LOW, the 3-State B output buffers are active and reflect the data present at the output of the A latches. Control of data flow from B to A is symetric to that above, but uses the EBA, LEBA, and OEBA inputs.

- Designed for 2.7 to 3.6V V_{CC} Operation
- 5.2ns Maximum tpd
- 5V Tolerant Interface Capability With 5V TTL Logic
- Supports Live Insertion and Withdrawal
- IOFF Specification Guarantees High Impedance When VCC = 0V
- LVTTL Compatible
- LVCMOS Compatible
- 24mA Balanced Output Sink and Source Capability
- Near Zero Static Supply Current in All Three Logic States (20μA) Substantially Reduces System Power Requirements
- Latchup Performance Exceeds 500mA
- ESD Performance: Human Body Model >2000V; Machine Model >200V



PIN NAMES

Pins	Function
OExxn	Output Enable Inputs
Exxn	Enable Inputs
LExxn	Latch Enable Inputs
A0–A15	3–State Inputs/Outputs
B0–B15	3–State Inputs/Outputs

This document contains information on a new product. Specifications and information herein are subject to change without notice.



11/96

DETAIL A 52 D B0 Q LE D 5 A0 -Q LE DETAIL A x 7 56 1 OEBA1 OEAB1 EBA1 EAB1 54 3 LEAB1 LEBA1 55 2 DETAIL B D 42 Q B8 LE D 15 A8 -Q LE DETAIL Bx 7 28 29 OEBA2 OEAB2

LOGIC DIAGRAM

OEAB1	1	0	0	56	OEBA1
LEAB1	2			55	LEBA1
EAB1	3			54	EBA1
GND	4			53	GND
A0	5			52	B0
A1	6			51	B1
Vcc	7			50	VCC
A2	8			49	B2
A3	9			48	B3
A4	10			47	B4
GND	11			46	GND
A5	12			45	B5
A6	13			44	B6
A7	14			43	B7
A8	15			42	B8
A9	16			41	B9
A10	17			40	B10
GND	18			39	GND
A11	19			38	B11
A12	20			37	B12
A13	21			36	B13
Vcc	22			35	VCC
A14	23			34	B14
A15	24			33	B15
GND	25			32	GND
EAB2				31	EBA2
LEAB2				30	LEBA2
OEAB2	28			29	OEBA2

Pinout: 56-Lead TSSOP (Top View)

EBA2

LEBA2

31

30

EAB2

LEAB2

26

27

FUNCTION TABLE

		Inpu	uts			Data	Ports	Operating Mede
OEABn	OEBAn	EABn	EBAn	LEABn	LEBAn	An	Bn	Operating Mode
Н	Н					Input	Input	
		Х	Х	Х	Х	Х	Х	Disable Outputs
		L	L	L	L	Х	Х	Transparent Data; Outputs Disabled
				н	Н	l h	l h	Latch and Outputs Disabled
L	Н					Input	Output	
		Н	Х*	L	Х	l h	Z Z	Load and B Outputs Disabled
				н	Х	Х	Z	Hold; B Outputs Disabled
		L	Х*	L	Х	L H	L H	Transparent A to B
				н	Х	l h	L H	Latch and Display B Outputs
Н	L					Output	Input	
		Х*	Н	Х	L	Z Z	l h	Load and A Outputs Disabled
				Х	Н	Z	Х	Hold; A Outputs DIsabled
		Х*	L	Х	L	L H	L H	Transparent B to A
				Х	Н	L H	l h	Latch and Display A Outputs

H = High Voltage Level; h = High Voltage Level One Setup Time Prior to the Latch Enable or Enable Low-to-High Transition; L = Low Voltage Level; I = Low Voltage Level One Setup Time Prior to the Latch Enable or Enable Low-to-High Transition; X = Don't Care; * = The latches are not internally gated with the Output Enables. Therefore, data at the A or B ports may enter the latches at any time, provided that the LExx and Exx pins are set accordingly. For ICC reasons, Do Not Float Inputs.

ABSOLUTE MAXIMUM RATINGS*

Symbol	Parameter	Value	Condition	Unit
VCC	DC Supply Voltage	-0.5 to +7.0		V
VI	DC Input Voltage	$-0.5 \leq V_{I} \leq +7.0$		V
VO	DC Output Voltage	$-0.5 \le V_O \le +7.0$	Output in 3–State	V
		$-0.5 \leq V_O \leq V_{CC} + 0.5$	Note 1.	V
liк	DC Input Diode Current	-50	V _I < GND	mA
Іок	DC Output Diode Current	-50	V _O < GND	mA
		+50	AO > ACC	mA
lo	DC Output Source/Sink Current	±50		mA
Icc	DC Supply Current Per Supply Pin	±100		mA
IGND	DC Ground Current Per Ground Pin	±100		mA
T _{STG}	Storage Temperature Range	-65 to +150		°C

* Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute-maximum-rated conditions is not implied.

1. Output in HIGH or LOW State. IO absolute maximum rating must be observed.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Тур	Max	Unit
VCC	Supply Voltage Operating Data Retention Only	2.0 1.5	3.3 3.3	3.6 3.6	V
VI	Input Voltage	0		5.5	V
VO	Output Voltage (HIGH or LOW State) (3–State)	0 0		V _{CC} 5.5	V
ЮН	HIGH Level Output Current, V _{CC} = 3.0V – 3.6V			-24	mA
IOL	LOW Level Output Current, $V_{CC} = 3.0V - 3.6V$			24	mA
ЮН	HIGH Level Output Current, $V_{CC} = 2.7V - 3.0V$			-12	mA
IOL	LOW Level Output Current, $V_{CC} = 2.7V - 3.0V$			12	mA
Т _А	Operating Free–Air Temperature	-40		+85	°C
Δt/ΔV	Input Transition Rise or Fall Rate, V _{IN} from 0.8V to 2.0V, V _{CC} = $3.0V$	0		10	ns/V

DC ELECTRICAL CHARACTERISTICS

			T _A = −40°C	to +85°C	
Symbol	Characteristic	Condition	Min	Max	Unit
VIH	HIGH Level Input Voltage (Note 2.)	$2.7V \le V_{CC} \le 3.6V$	2.0		V
VIL	LOW Level Input Voltage (Note 2.)	$2.7V \le V_{CC} \le 3.6V$		0.8	V
VOH	HIGH Level Output Voltage	$2.7V \le V_{CC} \le 3.6V; I_{OH} = -100\mu A$	V _{CC} – 0.2		V
		V _{CC} = 2.7V; I _{OH} = -12mA	2.2		
		V _{CC} = 3.0V; I _{OH} = -18mA	2.4		
		V _{CC} = 3.0V; I _{OH} = -24mA	2.2		
VOL	LOW Level Output Voltage	$2.7V \le V_{CC} \le 3.6V$; $I_{OL} = 100\mu A$		0.2	V
		V _{CC} = 2.7V; I _{OL} = 12mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 16mA		0.4	
		V _{CC} = 3.0V; I _{OL} = 24mA		0.55	
l	Input Leakage Current	$2.7 \text{V} \leq \text{V}_{CC} \leq 3.6 \text{V}; \ 0 \text{V} \leq \text{V}_{I} \leq 5.5 \text{V}$		±5.0	μA
I _{OZ}	3–State Output Current	$2.7 \le V_{CC} \le 3.6V; \ 0V \le V_O \le 5.5V;$ $V_I = V_{IH} \ or \ V_{IL}$		±5.0	μA
IOFF	Power-Off Leakage Current	$V_{CC} = 0V; V_I \text{ or } V_O = 5.5V$		10	μA
ICC	Quiescent Supply Current	$2.7 \le V_{CC} \le 3.6$ V; V _I = GND or V _{CC}		20	μΑ
		$2.7 \le V_{CC} \le 3.6V$; $3.6 \le V_I$ or $V_O \le 5.5V$		±20	μΑ
∆ICC	Increase in I _{CC} per Input	$2.7 \le V_{CC} \le 3.6V; V_{IH} = V_{CC} - 0.6V$		500	μA

2. These values of V_{I} are used to test DC electrical characteristics only.

				Lin	nits			
		I [T _A = −40°C to +85°C				
			V _{CC} = 3.	0V to 3.6V	Vcc	= 2.7V		
Symbol	Parameter	Waveform	Min	Max	Min	Max	Unit	
^t PLH ^t PHL	Propagation Delay An to Bn or Bn to An	1	1.5 1.5	5.2 5.2	1.5 1.5	6.0 6.0	ns	
^t PLH ^t PHL	Propagation Delay LEBAn to An or LEABn to Bn	4	1.5 1.5	6.5 6.5	1.5 1.5	7.5 7.5	ns	
^t PZH ^t PZL	Output Enable Time OEBAn to An or OEABn to Bn	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns	
^t PHZ ^t PLZ	Output Disable T <u>ime</u> OEBAn to An or OEABn to Bn	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns	
^t PZH ^t PZL	Output Enable Time EBAn to An or EABn to Bn	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns	
^t PHZ ^t PLZ	Output Disable <u>Time</u> EBAn to An or EABn to Bn	2	1.5 1.5	6.5 6.5	1.5 1.5	7.0 7.0	ns	
t _s	Setup Time, HIGH to LOW Data to LExxn	4	2.5		2.5		ns	
t _h	Hold Time, HIGH to LOW Data to LExxn	4	1.5		1.5		ns	
t _S	Setup Time, HIGH to LOW Data to Exxn	4	2.5		2.5		ns	
t _h	Hold Time, HIGH to LOW Data to Exxn	4	1.5		1.5		ns	
tw	Latch Enable or Enable Pulse Width, LOW	4	3.0		3.0		ns	
^t OSHL ^t OSLH	Output-to-Output Skew (Note 4.)			1.0 1.0			ns	

AC CHARACTERISTICS (Note 3.; $t_R = t_F = 2.5ns$; $C_L = 50pF$; $R_L = 500\Omega$)

3. These AC parameters are preliminary and may be modified prior to release. The maximum AC limits are design targets. Actual performance will be specified upon completion of characterization.

4. Skew is defined as the absolute value of the difference between the actual propagation delay for any two separate outputs of the same device. The specification applies to any outputs switching in the same direction, either HIGH–to–LOW (t_{OSHL}) or LOW–to–HIGH (t_{OSLH}); parameter guaranteed by design.

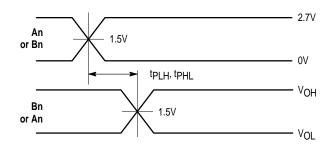
DYNAMIC SWITCHING CHARACTERISTICS

			Ţ	A = +25°	С	
Symbol	Characteristic	Condition	Min	Тур	Max	Unit
VOLP	Dynamic LOW Peak Voltage (Note 5.)	$V_{\mbox{\scriptsize CC}}$ = 3.3V, $C_{\mbox{\scriptsize L}}$ = 50pF, $V_{\mbox{\scriptsize IH}}$ = 3.3V, $V_{\mbox{\scriptsize IL}}$ = 0V		0.8		V
V _{OLV}	Dynamic LOW Valley Voltage (Note 5.)	V_{CC} = 3.3V, C_{L} = 50pF, V_{IH} = 3.3V, V_{IL} = 0V		0.8		V

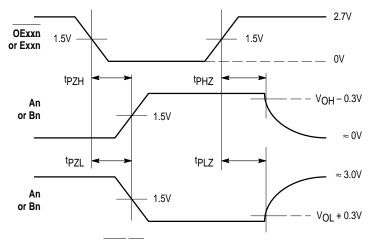
5. Number of outputs defined as "n". Measured with "n-1" outputs switching from HIGH-to-LOW or LOW-to-HIGH. The remaining output is measured in the LOW state.

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Condition	Typical	Unit
C _{IN}	Input Capacitance	$V_{CC} = 3.3V$, $V_I = 0V$ or V_{CC}	7	pF
C _{I/O}	Input/Output Capacitance	$V_{CC} = 3.3$ V, $V_{I} = 0$ V or V_{CC}	8	pF
C _{PD}	Power Dissipation Capacitance	10MHz, V _{CC} = 3.3V, V _I = 0V or V _{CC}	20	pF



WAVEFORM 1 – A/B to B/A PROPAGATION DELAYS $t_R = t_F = 2.5ns, 10\% to 90\%; f = 1MHz; t_W = 500ns$



WAVEFORM 2 – OExx/Exx to A or B OUTPUT ENABLE AND DISABLE TIMES $t_R = t_F = 2.5ns$, 10% to 90%; f = 1MHz; $t_W = 500ns$

Figure 1. AC Waveforms

2.7V

1.5V

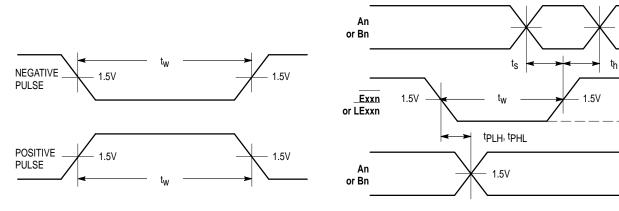
0V

· 2.7V

0V

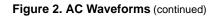
VOH

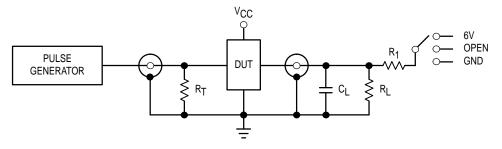
VOL



WAVEFORM 3 - INPUT PULSE DEFINITION $t_R = t_F = 2.5$ ns, 10% to 90% of 0V to 2.7V

WAVEFORM 4 - Enable to A or B PROPAGATION DELAYS, Enable MINIMUM PULSE WIDTH, A or B to Enable SETUP AND HOLD TIMES $t_R = t_F = 2.5ns$, 10% to 90%; f = 1MHz; $t_W = 500ns$ except when noted



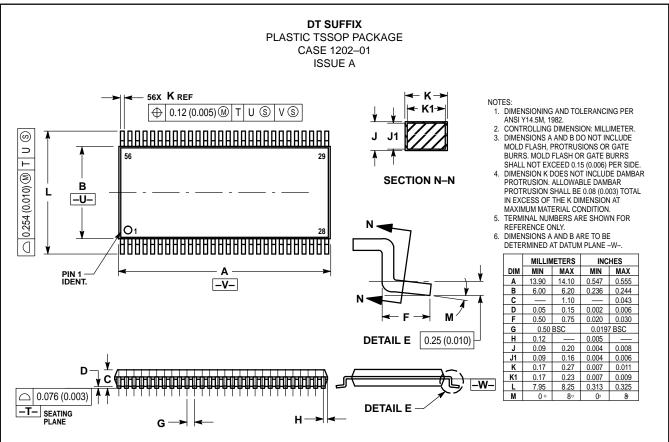


TEST	SWITCH
^t PLH ^{, t} PHL	Open
tPZL, tPLZ	6V
Open Collector/Drain tPLH and tPHL	6V
^t PZH ^{, t} PHZ	GND

 $\begin{array}{l} C_L = 50 pF \mbox{ or equivalent (Includes jig and probe capacitance)} \\ R_L = R_1 = 500 \Omega \mbox{ or equivalent} \\ R_T = Z_{OUT} \mbox{ of pulse generator (typically 50 \Omega)} \end{array}$

Figure 3. Test Circuit

OUTLINE DIMENSIONS



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